

LMC660 CMOS Quad Operational Amplifier

General Description

The LMC660 CMOS Quad operational amplifier is ideal for operation from a single supply. It operates from +5V to +15V and features rail-to-rail output swing in addition to an input common-mode range that includes ground. Performance limitations that have plagued CMOS amplifiers in the past are not a problem with this design. Input V_{OS} , drift, and broadband noise as well as voltage gain into realistic loads (2 k Ω and 600 Ω) are all equal to or better than widely accepted bipolar equivalents.

This chip is built with National's advanced Double-Poly Silicon-Gate CMOS process.

See the LMC662 datasheet for a dual CMOS operational amplifier with these same features.

Features

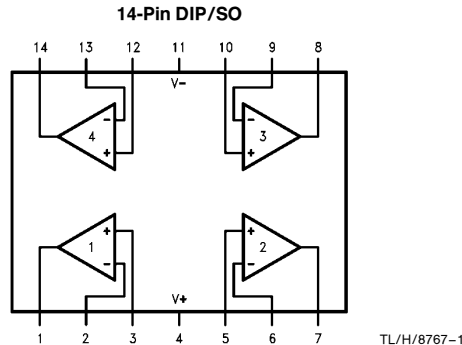
- Rail-to-rail output swing
- Specified for 2 k Ω and 600 Ω loads
- High voltage gain 126 dB
- Low input offset voltage 3 mV

- Low offset voltage drift 1.3 μ V/ $^{\circ}$ C
- Ultra low input bias current 2 fA
- Input common-mode range includes V^-
- Operating range from +5V to +15V supply
- $I_{SS} = 375 \mu$ A/amplifier; independent of V^+
- Low distortion 0.01% at 10 kHz
- Slew rate 1.1 V/ μ s
- Available in extended temperature range (-40° C to $+125^{\circ}$ C); ideal for automotive applications
- Available to Standard Military Drawing specification

Applications

- High-impedance buffer or preamplifier
- Precision current-to-voltage converter
- Long-term integrator
- Sample-and-Hold circuit
- Peak detector
- Medical instrumentation
- Industrial controls
- Automotive sensors

Connection Diagram



Ordering Information

Package	Temperature Range				NSC Drawing	Transport Media
	Military -55° C to $+125^{\circ}$ C	Extended -40° C + 125° C	Industrial -40° C to $+85^{\circ}$ C	Commercial 0° C to $+70^{\circ}$ C		
14-Pin Ceramic DIP	LMC660AMJ/883				J14A	Rail
14-Pin Small Outline		LMC660EM	LMC660AIM	LMC660CM	M14A	Rail Tape and Reel
14-Pin Molded DIP		LMC660EN	LMC660AIN	LMC660CN	N14A	Rail
14-Pin Side Brazed Ceramic DIP	LMC660AMD				D14E	Rail

Absolute Maximum Ratings (Note 3)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Differential Input Voltage	± Supply Voltage
Supply Voltage	16V
Output Short Circuit to V ⁺	(Note 12)
Output Short Circuit to V ⁻	(Note 1)
Lead Temperature (Soldering, 10 sec.)	260°C
Storage Temp. Range	-65°C to +150°C
Voltage at Input/Output Pins (V ⁺) + 0.3V, (V ⁻) - 0.3V	
Current at Output Pin	± 18 mA
Current at Input Pin	± 5 mA
Current at Power Supply Pin	35 mA

Power Dissipation	(Note 2)
Junction Temperature	150°C
ESD tolerance (Note 8)	1000V

Operating Ratings

Temperature Range	
LMC660AMJ/883,	-55°C ≤ T _J ≤ +125°C
LMC660AMD	-40°C ≤ T _J ≤ +85°C
LMC660AI	0°C ≤ T _J ≤ +70°C
LMC660C	-40°C ≤ T _J ≤ +125°C
LMC660E	
Supply Voltage Range	4.75V to 15.5V
Power Dissipation	(Note 10)
Thermal Resistance (θ _{JA}) (Note 11)	
14-Pin Ceramic DIP	90°C/W
14-Pin Molded DIP	85°C/W
14-Pin SO	115°C/W
14-Pin Side Brazed Ceramic DIP	90°C/W

DC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for T_J = 25°C. **Boldface** limits apply at the temperature extremes. V⁺ = 5V, V⁻ = 0V, V_{CM} = 1.5V, V_O = 2.5V and R_L > 1M unless otherwise specified.

Parameter	Conditions	Typ (Note 4)	LMC660AMD LMC660AMJ/883	LMC660AI	LMC660C	LMC660E	Units
			Limit (Notes 4, 9)	Limit (Note 4)	Limit (Note 4)	Limit (Note 4)	
Input Offset Voltage		1	3 3.5	3 3.3	6 6.3	6 6.5	mV max
Input Offset Voltage Average Drift		1.3					μV/°C
Input Bias Current		0.002	20 100	4	2	60	pA max
Input Offset Current		0.001	20 100	2	1	60	pA max
Input Resistance		> 1					TeraΩ
Common Mode Rejection Ratio	0V ≤ V _{CM} ≤ 12.0V V ⁺ = 15V	83	70 68	70 68	63 62	63 60	dB min
Positive Power Supply Rejection Ratio	5V ≤ V ⁺ ≤ 15V V _O = 2.5V	83	70 68	70 68	63 62	63 60	dB min
Negative Power Supply Rejection Ratio	0V ≤ V ⁻ ≤ -10V	94	84 82	84 83	74 73	74 70	dB min
Input Common-Mode Voltage Range	V ⁺ = 5V & 15V For CMRR ≥ 50 dB	-0.4	-0.1 0	-0.1 0	-0.1 0	-0.1 0	V max
		V ⁺ - 1.9	V ⁺ - 2.3 V⁺ - 2.6	V ⁺ - 2.3 V⁺ - 2.5	V ⁺ - 2.3 V⁺ - 2.4	V ⁺ - 2.3 V⁺ - 2.6	V min
Large Signal Voltage Gain	R _L = 2 kΩ (Note 5) Sourcing	2000	400 300	440 400	300 200	200 100	V/mV min
		Sinking	500	180 70	180 120	90 80	90 40
	R _L = 600Ω (Note 5) Sourcing	1000	200 150	220 200	150 100	100 75	V/mV min
		Sinking	250	100 35	100 60	50 40	50 20

DC Electrical Characteristics (Continued)

Unless otherwise specified, all limits guaranteed for $T_J = 25^\circ\text{C}$. **Boldface** limits apply at the temperature extremes. $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_{\text{CM}} = 1.5\text{V}$, $V_O = 2.5\text{V}$ and $R_L > 1\text{M}$ unless otherwise specified.

Parameter	Conditions	Typ (Note 4)	LMC660AMD LMC660AMJ/883	LMC660AI	LMC660C	LMC660E	Units
			Limit (Notes 4, 9)	Limit (Note 4)	Limit (Note 4)	Limit (Note 4)	
Output Swing	$V^+ = 5\text{V}$ $R_L = 2\text{ k}\Omega$ to $V^+ / 2$	4.87	4.82 4.77	4.82 4.79	4.78 4.76	4.78 4.70	V min
		0.10	0.15 0.19	0.15 0.17	0.19 0.21	0.19 0.25	V max
	$V^+ = 5\text{V}$ $R_L = 600\Omega$ to $V^+ / 2$	4.61	4.41 4.24	4.41 4.31	4.27 4.21	4.27 4.10	V min
		0.30	0.50 0.63	0.50 0.56	0.63 0.69	0.63 0.75	V max
	$V^+ = 15\text{V}$ $R_L = 2\text{ k}\Omega$ to $V^+ / 2$	14.63	14.50 14.40	14.50 14.44	14.37 14.32	14.37 14.25	V min
		0.26	0.35 0.43	0.35 0.40	0.44 0.48	0.44 0.55	V max
$V^+ = 15\text{V}$ $R_L = 600\Omega$ to $V^+ / 2$	13.90	13.35 13.02	13.35 13.15	12.92 12.76	12.92 12.60	V min	
	0.79	1.16 1.42	1.16 1.32	1.45 1.58	1.45 1.75	V max	
Output Current $V^+ = 5\text{V}$	Sourcing, $V_O = 0\text{V}$	22	16 12	16 14	13 11	13 9	mA min
	Sinking, $V_O = 5\text{V}$	21	16 12	16 14	13 11	13 9	mA min
Output Current $V^+ = 15\text{V}$	Sourcing, $V_O = 0\text{V}$	40	19 19	28 25	23 21	23 15	mA min
	Sinking, $V_O = 13\text{V}$ (Note 12)	39	19 19	28 24	23 20	23 15	mA min
Supply Current	All Four Amplifiers $V_O = 1.5\text{V}$	1.5	2.2 2.9	2.2 2.6	2.7 2.9	2.7 3.0	mA max

AC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $T_J = 25^\circ\text{C}$. **Boldface** limits apply at the temperature extremes. $V^+ = 5\text{V}$, $V^- = 0\text{V}$, $V_{\text{CM}} = 1.5\text{V}$, $V_{\text{O}} = 2.5\text{V}$ and $R_{\text{L}} > 1\text{M}$ unless otherwise specified.

Parameter	Conditions	Typ (Note 4)	LMC660AMD LMC660AMJ/883	LMC660AI	LMC660C	LMC660E	Units
			Limit (Notes 4, 9)	Limit (Note 4)	Limit (Note 4)	Limit (Note 4)	
Slew Rate	(Note 6)	1.1	0.8 0.5	0.8 0.6	0.8 0.7	0.8 0.4	V/ μs min
Gain-Bandwidth Product		1.4	0.5				MHz
Phase Margin		50					Deg
Gain Margin		17					dB
Amp-to-Amp Isolation	(Note 7)	130					dB
Input Referred Voltage Noise	F = 1 kHz	22					nV/ $\sqrt{\text{Hz}}$
Input Referred Current Noise	F = 1 kHz	0.0002					pA/ $\sqrt{\text{Hz}}$
Total Harmonic Distortion	F = 10 kHz, $A_V = -10$ $R_{\text{L}} = 2\text{k}\Omega$, $V_{\text{O}} = 8\text{V}_{\text{PP}}$ $V^+ = 15\text{V}$	0.01					%

Note 1: Applies to both single supply and split supply operation. Continuous short circuit operation at elevated ambient temperature and/or multiple Op Amp shorts can result in exceeding the maximum allowed junction temperature of 150°C . Output currents in excess of $\pm 30\text{mA}$ over long term may adversely affect reliability.

Note 2: The maximum power dissipation is a function of $T_{\text{J(max)}}$, θ_{JA} , and T_{A} . The maximum allowable power dissipation at any ambient temperature is $P_{\text{D}} = (T_{\text{J(max)}} - T_{\text{A}})/\theta_{\text{JA}}$.

Note 3: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

Note 4: Typical values represent the most likely parametric norm. Limits are guaranteed by testing or correlation.

Note 5: $V^+ = 15\text{V}$, $V_{\text{CM}} = 7.5\text{V}$ and R_{L} connected to 7.5V . For Sourcing tests, $7.5\text{V} \leq V_{\text{O}} \leq 11.5\text{V}$. For Sinking tests, $2.5\text{V} \leq V_{\text{O}} \leq 7.5\text{V}$.

Note 6: $V^+ = 15\text{V}$. Connected as Voltage Follower with 10V step input. Number specified is the slower of the positive and negative slew rates.

Note 7: Input referred. $V^+ = 15\text{V}$ and $R_{\text{L}} = 10\text{k}\Omega$ connected to $V^+/2$. Each amp excited in turn with 1kHz to produce $V_{\text{O}} = 13\text{V}_{\text{PP}}$.

Note 8: Human body model, $1.5\text{k}\Omega$ in series with 100pF .

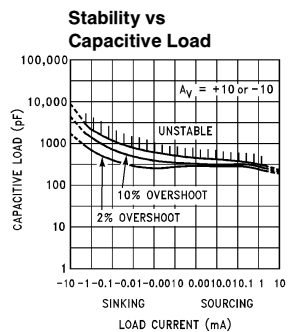
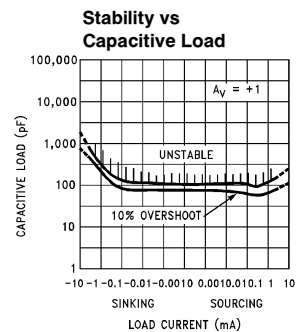
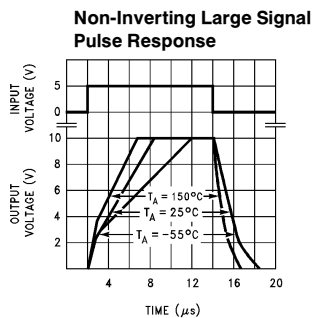
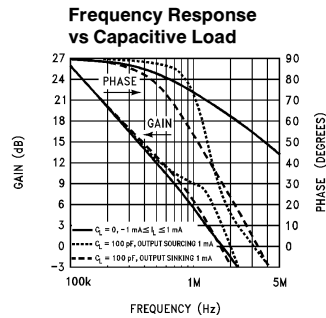
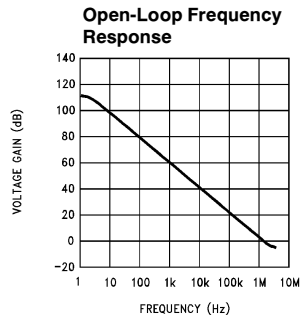
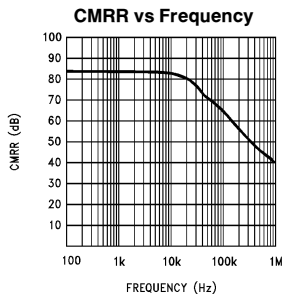
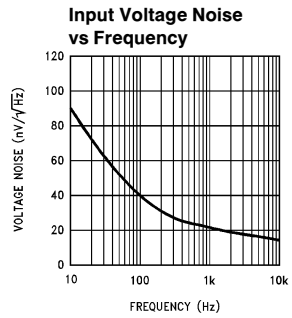
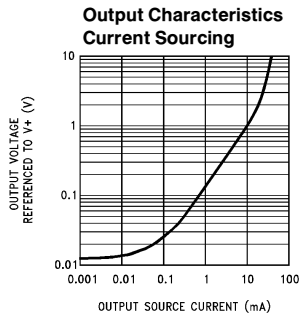
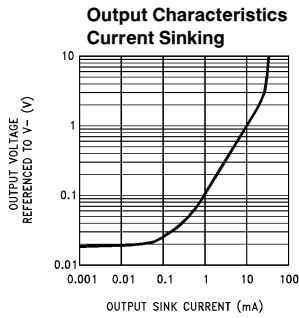
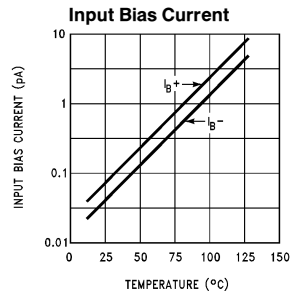
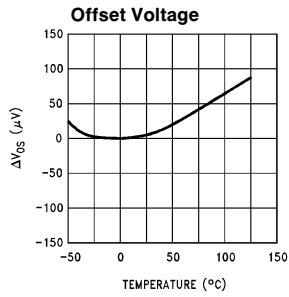
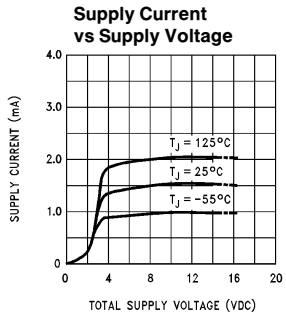
Note 9: A military RETS electrical test specification is available on request. At the time of printing, the LMC660AMJ/883 RETS spec complied fully with the boldface limits in this column. The LMC660AMJ/883 may also be procured to a Standard Military Drawing specification.

Note 10: For operating at elevated temperatures the device must be derated based on the thermal resistance θ_{JA} with $P_{\text{D}} = (T_{\text{J}} - T_{\text{A}})/\theta_{\text{JA}}$.

Note 11: All numbers apply for packages soldered directly into a PC board.

Note 12: Do not connect output to V^+ when V^+ is greater than 13V or reliability may be adversely affected.

Typical Performance Characteristics $V_S = \pm 7.5V, T_A = 25^\circ C$ unless otherwise specified



Note: Avoid resistive loads of less than 500Ω, as they may cause instability.

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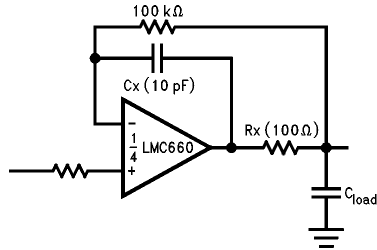
Application Hints (Continued)

Using the smaller capacitors will give much higher bandwidth with little degradation of transient response. It may be necessary in any of the above cases to use a somewhat larger feedback capacitor to allow for unexpected stray capacitance, or to tolerate additional phase shifts in the loop, or excessive capacitive load, or to decrease the noise or bandwidth, or simply because the particular circuit implementation needs more feedback capacitance to be sufficiently stable. For example, a printed circuit board's stray capacitance may be larger or smaller than the breadboard's, so the actual optimum value for C_F may be different from the one estimated using the breadboard. In most cases, the values of C_F should be checked on the actual circuit, starting with the computed value.

Capacitive Load Tolerance

Like many other op amps, the LMC660 may oscillate when its applied load appears capacitive. The threshold of oscillation varies both with load and circuit gain. The configuration most sensitive to oscillation is a unity-gain follower. See Typical Performance Characteristics.

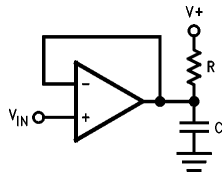
The load capacitance interacts with the op amp's output resistance to create an additional pole. If this pole frequency is sufficiently low, it will degrade the op amp's phase margin so that the amplifier is no longer stable at low gains. As shown in *Figure 3a*, the addition of a small resistor (50Ω to 100Ω) in series with the op amp's output, and a capacitor (5 pF to 10 pF) from inverting input to output pins, returns the phase margin to a safe value without interfering with lower-frequency circuit operation. Thus larger values of capacitance can be tolerated without oscillation. Note that in all cases, the output will ring heavily when the load capacitance is near the threshold for oscillation.



TL/H/8767-5

FIGURE 3a. Rx, Cx Improve Capacitive Load Tolerance

Capacitive load driving capability is enhanced by using a pull up resistor to V^+ (*Figure 3b*). Typically a pull up resistor conducting $500\ \mu\text{A}$ or more will significantly improve capacitive load responses. The value of the pull up resistor must be determined based on the current sinking capability of the amplifier with respect to the desired output swing. Open loop gain of the amplifier can also be affected by the pull up resistor (see Electrical Characteristics).



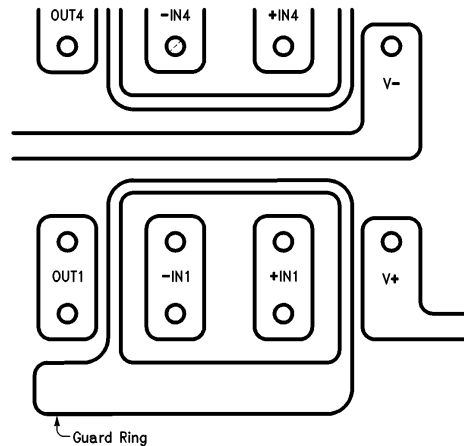
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FIGURE 3b. Compensating for Large Capacitive Loads with a Pull Up Resistor

PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK

It is generally recognized that any circuit which must operate with less than 1000 pA of leakage current requires special layout of the PC board. When one wishes to take advantage of the ultra-low bias current of the LMC662, typically less than 0.04 pA , it is essential to have an excellent layout. Fortunately, the techniques for obtaining low leakages are quite simple. First, the user must not ignore the surface leakage of the PC board, even though it may sometimes appear acceptably low, because under conditions of high humidity or dust or contamination, the surface leakage will be appreciable.

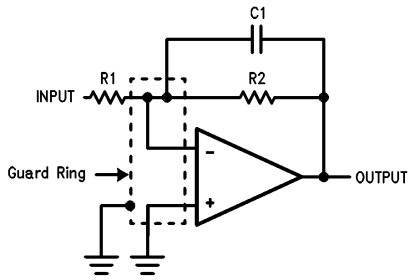
To minimize the effect of any surface leakage, lay out a ring of foil completely surrounding the LMC660's inputs and the terminals of capacitors, diodes, conductors, resistors, relay terminals, etc. connected to the op-amp's inputs. See *Figure 4*. To have a significant effect, guard rings should be placed on both the top and bottom of the PC board. This PC foil must then be connected to a voltage which is at the same voltage as the amplifier inputs, since no leakage current can flow between two points at the same potential. For example, a PC board trace-to-pad resistance of $10^{12}\Omega$, which is normally considered a very large resistance, could leak 5 pA if the trace were a 5V bus adjacent to the pad of an input. This would cause a 100 times degradation from the LMC660's actual performance. However, if a guard ring is held within 5 mV of the inputs, then even a resistance of $10^{11}\Omega$ would cause only 0.05 pA of leakage current, or perhaps a minor (2:1) degradation of the amplifier's performance. See *Figures 5a, 5b, 5c* for typical connections of guard rings for standard op-amp configurations. If both inputs are active and at high impedance, the guard can be tied to ground and still provide some protection; see *Figure 5d*.



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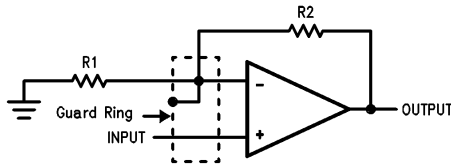
FIGURE 4. Example, using the LMC660, of Guard Ring in P.C. Board Layout

Application Hints (Continued)



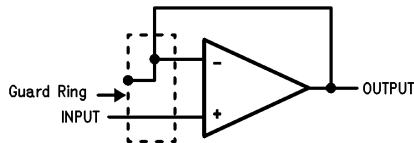
(a) Inverting Amplifier

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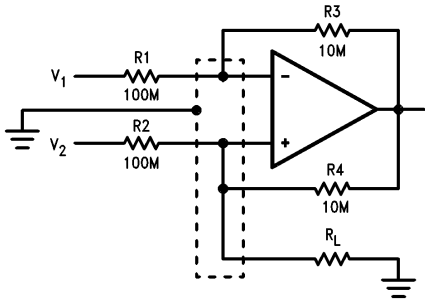
(b) Non-Inverting Amplifier

TL/H/8767-18



(c) Follower

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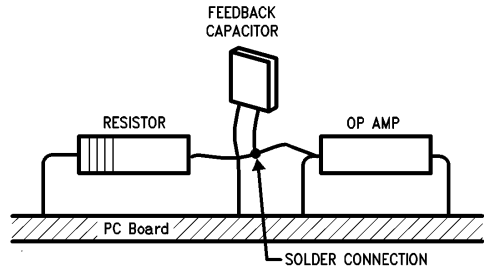
(d) Howland Current Pump

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FIGURE 5. Guard Ring Connections

The designer should be aware that when it is inappropriate to lay out a PC board for the sake of just a few circuits, there is another technique which is even better than a guard ring on a PC board: Don't insert the amplifier's input pin into the board at all, but bend it up in the air and use only air as an insulator. Air is an excellent insulator. In this case you may

have to forego some of the advantages of PC board construction, but the advantages are sometimes well worth the effort of using point-to-point up-in-the-air wiring. See Figure 6.



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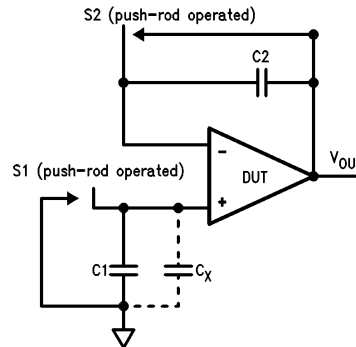
(Input pins are lifted out of PC board and soldered directly to components. All other pins connected to PC board.)

FIGURE 6. Air Wiring

BIAS CURRENT TESTING

The test method of Figure 7 is appropriate for bench-testing bias current with reasonable accuracy. To understand its operation, first close switch S2 momentarily. When S2 is opened, then

$$I_{b^-} = \frac{dV_{OUT}}{dt} \times C_2.$$



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FIGURE 7. Simple Input Bias Current Test Circuit

A suitable capacitor for C2 would be a 5 pF or 10 pF silver mica, NPO ceramic, or air-dielectric. When determining the magnitude of I_{b^-} , the leakage of the capacitor and socket must be taken into account. Switch S2 should be left shorted most of the time, or else the dielectric absorption of the capacitor C2 could cause errors.

Similarly, if S1 is shorted momentarily (while leaving S2 shorted)

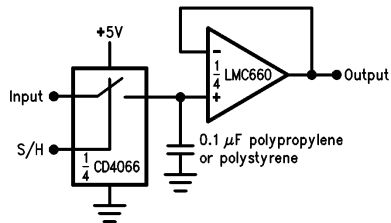
$$I_{b^+} = \frac{dV_{OUT}}{dt} \times (C_1 + C_x)$$

where C_x is the stray capacitance at the + input.

Typical Single-Supply Applications ($V^+ = 5.0 \text{ VDC}$)

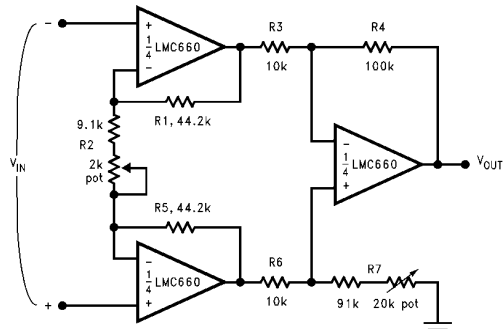
Additional single-supply applications ideas can be found in the LM324 datasheet. The LMC660 is pin-for-pin compatible with the LM324 and offers greater bandwidth and input resistance over the LM324. These features will improve the performance of many existing single-supply applications. Note, however, that the supply voltage range of the LMC660 is smaller than that of the LM324.

Low-Leakage Sample-and-Hold



TL/H/8767-7

Instrumentation Amplifier



TL/H/8767-8

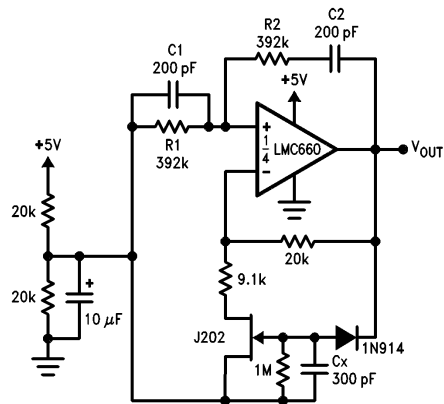
If $R1 = R5$, $R3 = R6$, and $R4 = R7$; then

$$\frac{V_{OUT}}{V_{IN}} = \frac{R2 + 2R1}{R2} \times \frac{R4}{R3}$$

$\therefore A_v \approx 100$ for circuit shown.

For good CMRR over temperature, low drift resistors should be used. Matching of $R3$ to $R6$ and $R4$ to $R7$ affect CMRR. Gain may be adjusted through $R2$. CMRR may be adjusted through $R7$.

Sine-Wave Oscillator

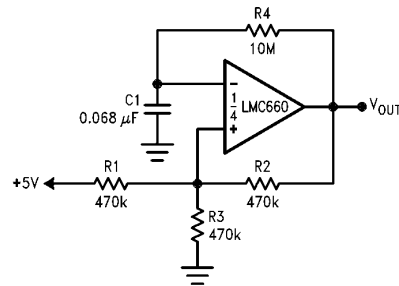


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Oscillator frequency is determined by $R1$, $R2$, $C1$, and $C2$:
 $f_{osc} = 1/2\pi RC$, where $R = R1 = R2$ and
 $C = C1 = C2$.

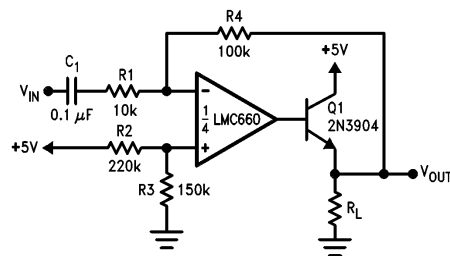
This circuit, as shown, oscillates at 2.0 kHz with a peak-to-peak output swing of 4.5V.

1 Hz Square-Wave Oscillator



TL/H/8767-10

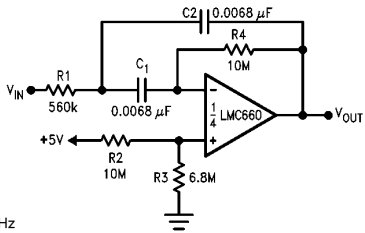
Power Amplifier



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Typical Single-Supply Applications ($V^+ = 5.0 \text{ VDC}$) (Continued)

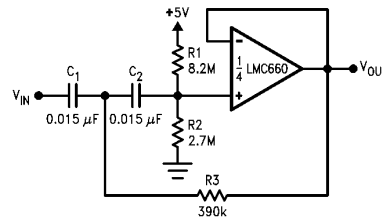
10 Hz Bandpass Filter



$f_c = 10 \text{ Hz}$
 $Q = 2.1$
 Gain = -8.8

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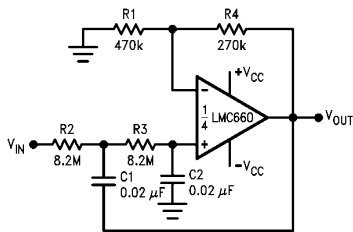
10 Hz High-Pass Filter



$f_c = 10 \text{ Hz}$
 $d = 0.895$
 Gain = 1
 2 dB passband ripple

TL/H/8767-13

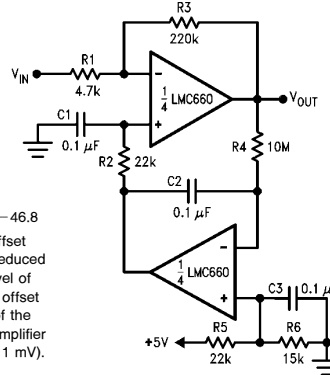
1 Hz Low-Pass Filter (Maximally Flat, Dual Supply Only)



$f_c = 1 \text{ Hz}$
 $d = 1.414$
 Gain = 1.57

TL/H/8767-14

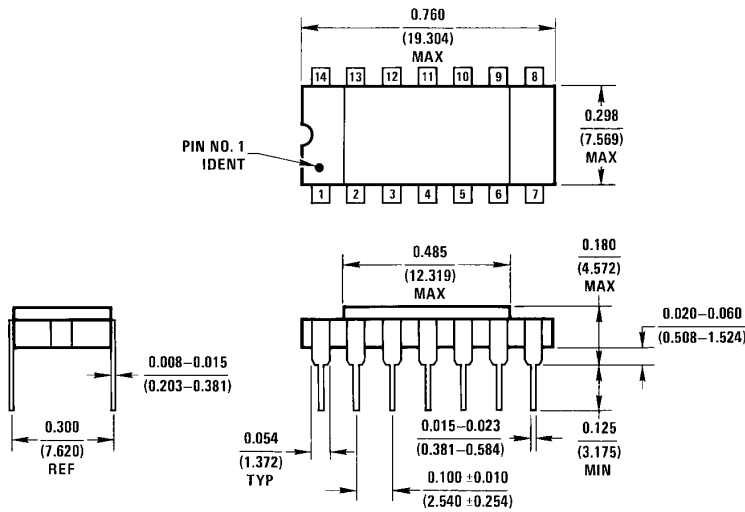
High Gain Amplifier with Offset Voltage Reduction



Gain = -46.8
 Output offset
 voltage reduced
 to the level of
 the input offset
 voltage of the
 bottom amplifier
 (typically 1 mV).

TL/H/8767-15

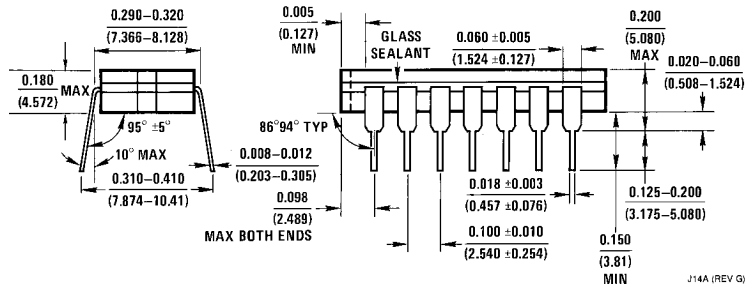
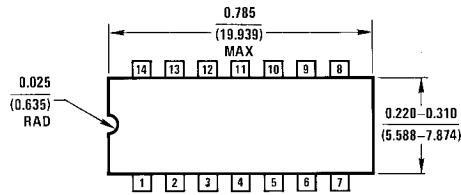
Physical Dimensions inches (millimeters)



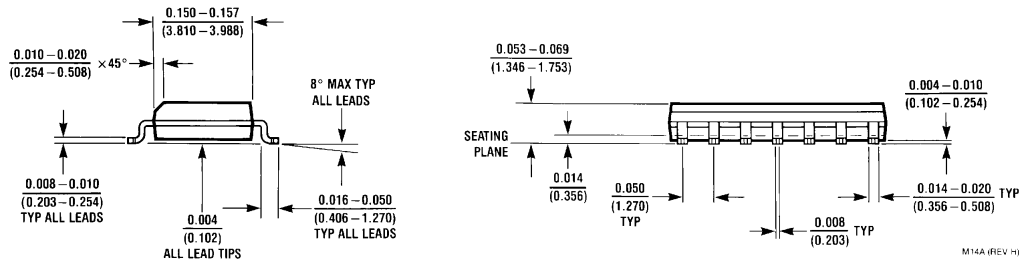
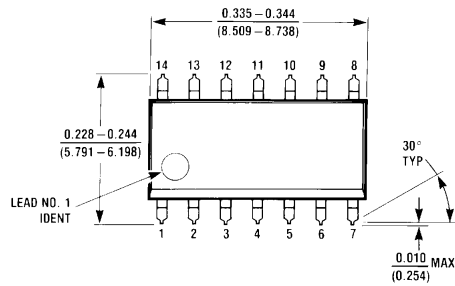
14-Lead Hermetic Dual-In-Line Package (D)
 Order Number LMC660AMD
 NS Package Number D14E

D14E (REV E)

Physical Dimensions inches (millimeters) (Continued)

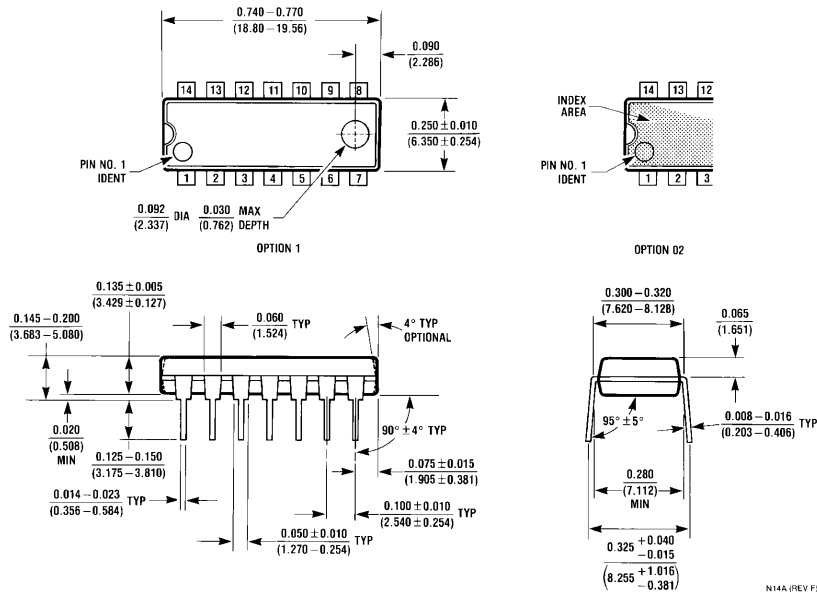


14-Lead Ceramic Dual-In-Line Pkg. (J)
Order Number LMC660AMJ/883
NS Package Number J14A



Small Outline Dual-In-Line Pkg. (M)
Order Number LMC660AIM, LMC660CM or LMC660EM
NS Package Number M14A

Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Pkg. (N)
Order Number LMC660AIN, LMC660CN or LMC660EN
NS Package Number N14A

LIFE SUPPORT POLICY

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



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